

N-channel 60 V 11.3 mΩ standard level MOSFET in LFPAK33 4 June 2013 Product data sheet

1. General description

Standard level enhancement mode N-channel MOSFET in LFPAK33 package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

2. Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources
- LFPAK33 package is footprint compatible with other 3.3mm types
- Qualified to 175 °C

3. Applications

- AC-to-DC converters
- Synchronous rectification
- DC-DC converters

4. Quick reference data

Table 1. Q	uick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C	-	-	60	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	-	61	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	91	W
Tj	junction temperature		-55	-	175	°C
Static chara	octeristics	1	I			
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 12	-	9.6	11.3	mΩ
Dynamic ch	aracteristics	1	I			
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I _D = 15 A; V _{DS} = 30 V; T _j = 25 °C; Fig. 14; Fig. 15	-	5.8	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		D
2	S	source		
3	S	source		G-UTA
4	G	gate		mbb076 S
mb	D	mounting base; connected to drain	LFPAK33 (SOT1210)	

6. Ordering information

Table 3. Ordering in	able 3. Ordering information					
Type number	Package					
	Name	Description	Version			
PSMN011-60MS	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 4 leads	SOT1210			

7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN011-60MS	M11S60

8. Limiting values

Table 5. Limiting values

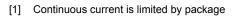
In accordance with the Absolute Maximum Rating System (IEC 60134).

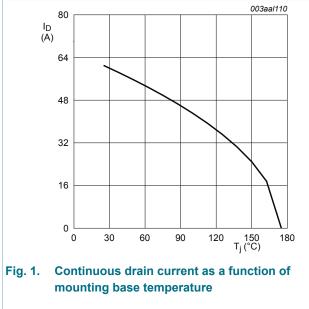
Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C	-	60	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	-	61	А
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 1</u>	-	43	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 4	-	244	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	91	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drai	in diode		1			
I _S	source current	T _{mb} = 25 °C	[1]	-	70	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	244	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:VGS} \begin{array}{l} V_{GS} \texttt{=} 10 \; V; \; T_{j(\text{init})}\texttt{=} 25 \; ^\circ \texttt{C}; \; I_{D}\texttt{=} 61 \; A; \\ V_{sup} \texttt{\leq} 60 \; V; \; R_{GS}\texttt{=} 50 \; \Omega; \; unclamped; \\ \hline Fig. 3 \end{array}$		-	48.1	mJ





 $V_{GS} \ge 10V$

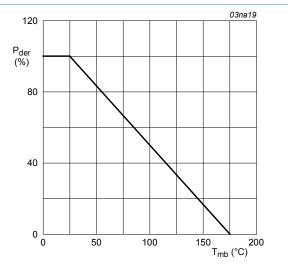
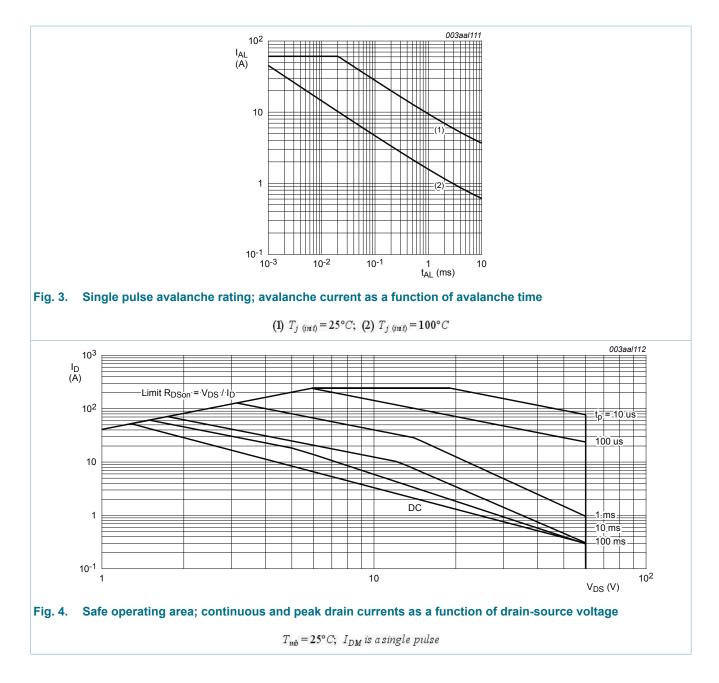


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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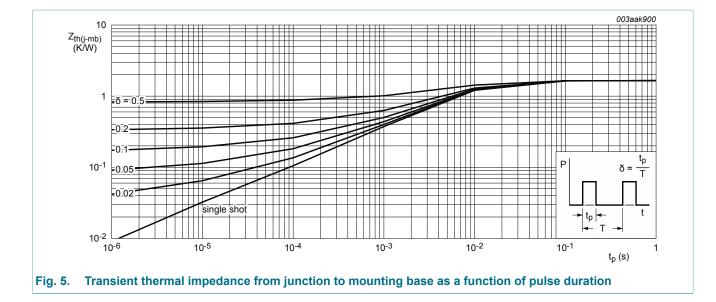


9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	1.44	1.65	K/W

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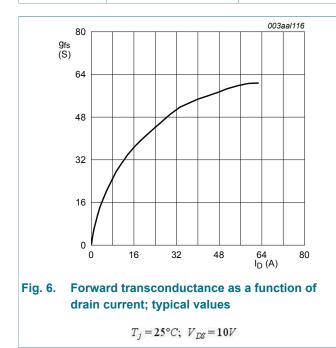


10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	60	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	54	-	-	V
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; Fig. 10	1	-	-	V
V _{GSth}	GSth gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 10; Fig. 11	2.3	3	4	V
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.6	V	
I _{DSS} drain leakage current	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C	-	0.054	1	μA
	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA	
GSS gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA	
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 12	-	9.6	11.3	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 175 °C; Fig. 13	-	-	24.4	mΩ
R _G	gate resistance	f = 1 MHz	-	2.75	-	Ω
Dynamic cł	naracteristics	· · ·	I			
Q _{G(tot)}	total gate charge	I _D = 15 A; V _{DS} = 30 V; V _{GS} = 10 V; T _i = 25 °C; <u>Fig. 14; Fig. 15</u>	-	23	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Q _{GS}	gate-source charge	I_D = 15 A; V_{DS} = 30 V; V_{GS} = 10 V;	-	6.1	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	3.9	-	nC
$Q_{GS(\text{th-pl})}$	post-threshold gate- source charge		-	2.2	-	nC
Q _{GD}	gate-drain charge		-	5.8	-	nC
C _{iss}	input capacitance	V_{DS} = 30 V; V_{GS} = 0 V; f = 1 MHz;	-	1368	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 16</u>	-	191	-	pF
C _{rss}	reverse transfer capacitance		-	108	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R _L = 2 Ω; V _{GS} = 10 V; R _{G(ext)} = 5 Ω; T _j = 25 °C	-	6.7	-	ns
t _r	rise time		-	8.46	-	ns
t _{d(off)}	turn-off delay time		-	16.9	-	ns
t _f	fall time		-	9.18	-	ns
Source-drai	in diode					
V _{SD}	source-drain voltage	I_{S} = 15 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 17</u>	-	0.84	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 15 A; dI_{\rm S}/dt = -100 A/µs; V _{GS} = 0 V;	-	21.7	-	ns
Q _r	recovered charge	V _{DS} = 30 V; T _j = 25 °C	-	19.2	-	nC
					1	



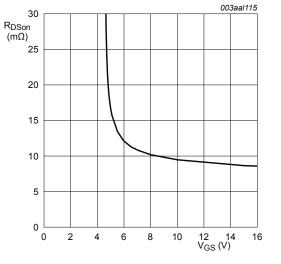
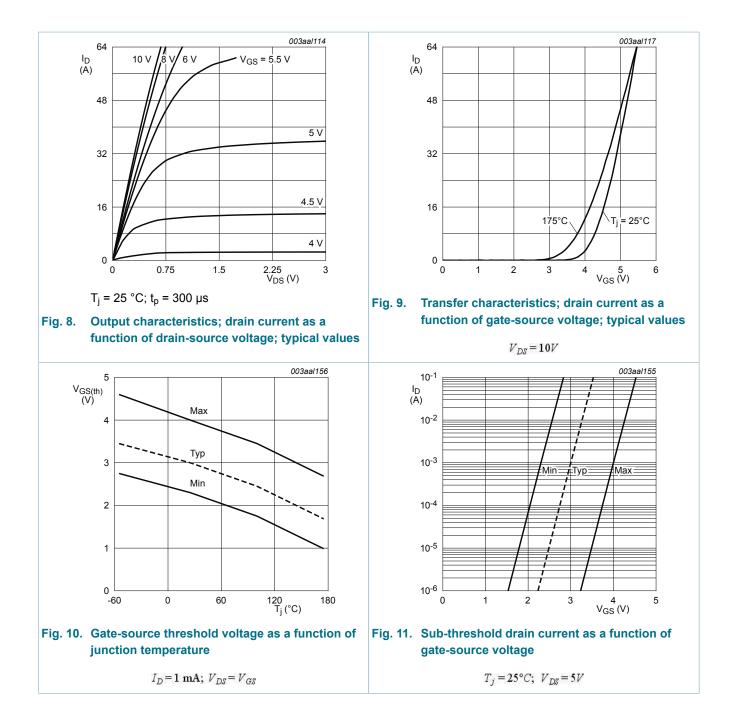


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; \ I_D = 15A$

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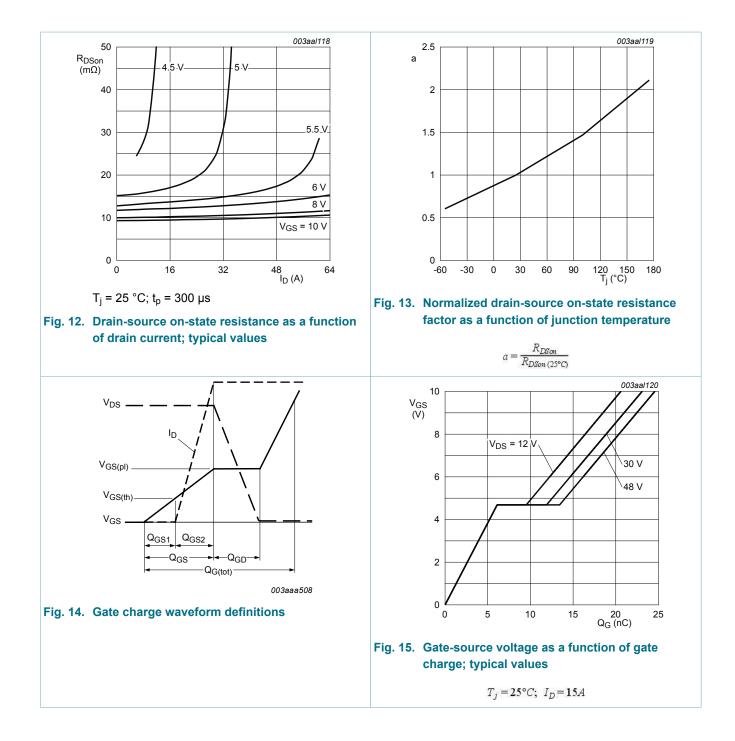
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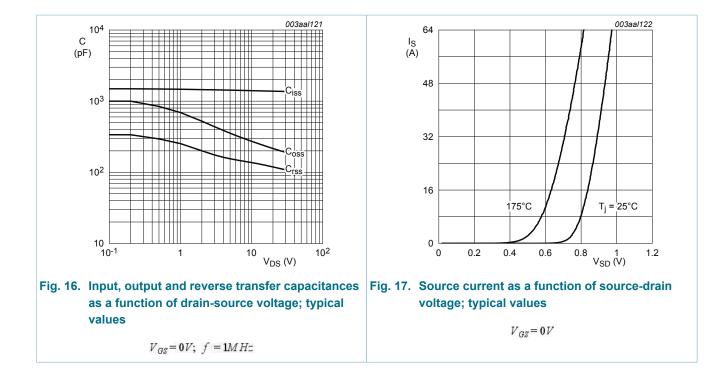
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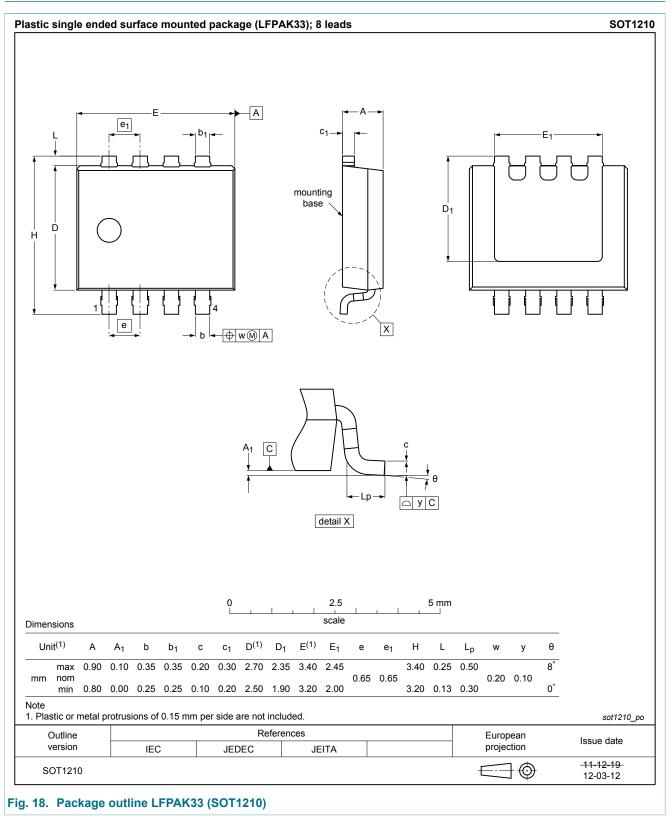
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11. Package outline



PSMN011-60MS

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12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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